

Recent Progress in the codes implementing Density Functional Theory

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Abstract

It is known that one of the traditional short comes of the codes based on Density Functional Theory is its impossibility to account for the band gap of semiconductors. This is the case of several known codes as Abinit, Siesta, Hamilt, and others. It is also the case for Wien 2K. Very recently, in the so call code Wien 2011, this difficulty was overcome. In this paper, we report our analysis of this recent progress. We have calculated, using this code, the band structure of several semiconductors and found an important improvement in the overall agreement with experiment which remains nevertheless in some very few cases as big as 20% off. In spite of it, this new progress opens the possibility for surface and interface calculations involving semiconductors which were not possible with the necessary accuracy using the former versions of any code implementing Density functional Theory and therefore some important findings remained uncertain. Further, the recommendation to optimize within the Local Density Approximation and to use the lattice constant found in this way into the new code to proceed with a calculation is analyzed in detail and found appropriate, It remains, nevertheless, according to us, as a point to fix in more detail in the future.

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I. INTRODUCTION

Density Functional Theory (*DFT*) is nowadays the most used method to calculate band structures. It is implemented in several codes. One very well known is the Wien2k code. It has evolved in several versions. A friendly interaction was produced already in the 2000 version. Nevertheless, a long standing problem of all the codes based on *DFT* was that the band structure of semiconductors, although giving a reasonable account of the dispersion of the bands, was systematically unable to reproduce the experimental values of the gap. This problem could be solved by hand using a trick but this kind of solution is not what we expect from an ab initio calculation. The removal of this problem in the new version (*Wien2k 2011*) is the subject of the analysis that we present in this work. The new ability to reproduce the gap value of semiconducting materials, allows confirming results for semiconductor/metal and semiconductor/semiconductor interfaces and to calculate new ones. These results are of technological interest and per se. For example, the *YBCO7/GaAs*(001) interface was calculated [1] using the previous version of the *Wien2k* code (2008 version) and two atomic planes in the GaAs side of the interface were found to be metallic. This result could, nevertheless, be influenced by the inability of the previous version of the code to properly account for the gap of the semiconductor. Since the trick mentioned above could not be used in an interface calculation, the result remained questionable because of the uncertainties in the *GaAs* side results around the very important gap region. The rest of the paper is organized as follows. In the next section II, we deal very briefly with Density Functional theory (*DFT*) to point to a detail important to this work. In section III, we briefly present a few of our calculated results for the band structure of metals to check that the accuracy of the new version remains the same also in this case. Section IV is devoted to semiconductors. We recalculate the results from references [2] and [3] and present new results for some other semiconductors which we compare to experiment. In a final section V, we analyze the results with the new code and present our conclusions.

II. DENSITY FUNCTIONAL THEORY

In solids, ions and electrons constitute a many body interacting system described by a Schrödinger equation with too many particle coordinates to be numerically treatable nowa-

days, as it is very well known. During the last decade, several codes were developed based on *DFT* and this method became the most used, precise and practical way to calculate the band structure of solids. The development of practical approximations to the correlation and interchange potential lead to a remarkable degree of accuracy to describe even complicated metallic systems. At the basis of *DFT* is the celebrated Hohenberg-Khon theorem which shows that the density of the ground state contains all the possible information on a system and its knowledge is equivalent to the wave function itself. So, the expectation value [4] of any observable can be calculated from a unique functional of the ground state density, $\rho(r)$, which minimizes the energy functional, $E[\rho]$. Further, Khon and Sham [5] transformed the many-body problem into a one-body problem and showed that the density of states calculated from the solution of the so-called Khon-Sham equations ((1)) is equal to the one of the real ground state density of the many-body system,

$$[T + V_H + V_{xc}]\varphi_i(r) = \varepsilon_i\varphi_i \quad (1)$$

Where the density is calculated taking into account the occupied states only. In eq. (1), T is the kinetic energy operator, V_H is the Hartree potential and V_{xc} is the exchange and correlation potential which is calculated from the exchange and correlation energy functional, $V_{xc}(r) = \frac{\delta E_{xc}[\rho]}{\delta \rho}$. To solve the Khon-Sham equations (1), an explicit expression for $E_{xc}[\rho]$ is needed. The exact expression is unknown since it includes all kind of correlations between all the particles in the system. So an approximation is needed. The first and best known approximation is Local Density Approximation, *LDA* [6], which was followed by the Generalized Gradient Approximation (*GGA*) and the *meta-GGA* [7] among other approximations. These potentials reproduce rather well the band structure of even complicated metallic systems but fail in reproducing the gap in semiconductors. A recent progress has been made. Blaha et al. [2] have reported the so-called *TB-MBJLDA* potential which is a modification of the exchange and correlation potential of Becke and Johnson (*BJ*) [8]. The new potential reproduces the experimental gaps with accuracy several orders of magnitude better than the former existing potentials. The modified *TB-MBJLDA* is

$$V_{x,\sigma}^{MBJ}(r) = cV_{x,\sigma}^{BR}(r) + (3c - 2)\frac{1}{\pi}\frac{\sqrt{5}}{12}\frac{\sqrt{2t_\sigma(r)}}{\rho_\sigma(r)} \quad (2)$$

Where $\rho_\sigma(r)$ is the density of states, $t_\sigma(r)$ is the kinetic energy density and $V_{x,\sigma}^{BJ}(r)$ is the Becke-Roussel potential (*BR*) [9]. The *c* stands for,

$$c = \alpha + \left(\beta \frac{1}{V_{cell}} \int d^3r \frac{|\nabla \rho(r)|}{\rho(r)} \right)^{1/2} \quad (3)$$

α and β are free parameters. Within the *Wien2k 2011* code $\alpha = -0.012$ and $\beta = 1.023 \text{ Bohr}^{1/2}$. We now proceed to present our results using the new *Wien2k 2011* code.

III. METAL CALCULATIONS

We present here our result for Nb, V and Ta, just to check whether differences arise between the old code and the new one for the case of metals. We have calculated these band structures, first, using the Full Potential-Linearized Plane Waves plus local orbitals (*FP-LAPW + lo*) approximation as implemented in the *Wien2k* code [10] and then we redid the same calculation using the new *MBJLDA* potential [2] implemented in the *Wien 2011* code. Some of the relevant parameters are presented in Table I.

TABLE I. The lattice parameter, *a*, in Angstrom; the Fermi energy, E_F , in Rydbergs; the density of states at E_F , $N(E_F)$ in states per Rydberg for Nb, V and Ta calculated with LDA and with MBJLDA. The experimental values were taken from reference [11].

Element	Experiment		LDA		MBJLDA		
	<i>a</i>	<i>a</i>	E_F	$N(E_F)$	<i>a</i>	E_F	$N(E_F)$
Nb	3.30059	3.2487	0.78890	24	3.2746	0.7535	23
V	3.02487	2.9273	0.67200	28.28	2.9574	0.6362	30.54
Ta	3.30280	3.2500	0.84131	21.20	3.3114	0.7950	21.95

We have made the corresponding optimization of the lattice parameter, *a*, using the same potential as to calculate the band structure and the density of states. As it can be appreciated from the table, some small but not negligible differences occur. This illustrates the need to follow the following procedure. To optimize the lattice parameter in a consistent way it is recommended [2] to use *LDA (GGA)* first and to use further the optimized lattice

parameter obtained in this way to compute with the *MBJLDA* new potential. If we follow this method, we find a better agreement between *LDA* and *MBJLDA* for all the three metals calculated as it can be checked from Table II.

TABLE II. Result of the new calculation optimizing both with *LDA*. The symbols and the units are the same as in Table I. Here we use the lattice parameter optimize with *LDA* for both calculations (see Table I).

Element	LDA		MBJLDA	
	E_F	$N(E_F)$	E_F	$N(E_F)$
Nb	0.78890	24	0.7785	22.15
V	0.67200	28.28	0.6734	29.24
Ta	0.84131	21.20	0.8572	20.78

Indeed, the Fermi energy for *Nb*, differs 0.01 Ry which represents 1.3% with respect to the *LDA* value which improves the 4.5% difference from Table I. For *V* and *Ta* these values are 0.2% and 1.8% which improve the 5.3% and 5.5% difference from Table I, respectively. So, we conclude that the recommendation given should be followed in any case, not only when dealing with semiconductor systems, to get better results when the use of the *MBJLDA* potential is compulsory as in the case of a metal/semiconductor interface, for example. The argument to it was given by Blaha et al. [2] in the sense that since there is no exchange functional, E_x , from which an exchange potential can be obtained, $V_{xc}(r) = \frac{\delta E_{xc}[\rho]}{\delta \rho}$, the procedure is justified. We omit the plot of the band structure and the density of states obtained in the different ways mentioned here since the overall agreement is such that the details just discussed do not show explicitly enough and these band structures are very well known. For *Nb* we have compared our results with references [12–14], *V* with references [14, 15] and for *Ta* with reference [16].

IV. SEMICONDUCTOR CALCULATIONS

In Table III, we present the gap value obtained from our band structure calculations for several semiconductors using *LDA* and the new *MBJLDA* as in the *Wien2k 2011* code and

TABLE III. The gap is in eV, the crystal structure is indicated in the second column, the data are from Blaha et al. [2], from HSE [3] and the experimental ones from references [2, 3, 17, 18].

Element	Structure	This work		Blaha et al.		HSE	Expt.
		LDA	MBJLDA	LDA	MBJLDA		
Si	A1	0.48	1.18	0.47	1.17	1.28	1.17
Ge	A1	0.00	0.86	0.00	0.85	0.56	0.74
MgO	B1	4.72	7.27	4.70	7.17	6.50	7.55
LiF	B1	8.78	13.10	8.94	12.94		14.20
AlAs	B3	1.35	2.16	1.40 ^a		2.24	2.23
SiC	B3	1.31	2.25	1.35	2.28	2.39	2.40
BP	B3	1.19	1.86	1.31 ^a		2.16	2.00
BAs	B3	1.23	1.71	1.16 ^a		1.92	1.46
InP	B3	0.45	1.57		1.40 ^b	1.64	1.43
AlP	B3	1.45	2.32	1.46	2.32	2.52	2.45
BN	B3	4.78	6.07	4.39	5.85	5.98	6.22
GaN	B3	1.66	2.80	1.63	2.81	3.03	3.20
CdTe	B3	0.49	1.65	0.61 ^a		1.52	1.49
GaAs	B3	0.30	1.64	0.30	1.64	1.21	1.52
ZnS	B3	1.83	3.63	1.84	3.66	3.42	3.91
CdS	B3	0.87	2.63	0.86	2.66	2.14	2.42
AlSb	B3	1.14	1.79	1.29 ^a		1.99	1.68
InN	B4	0.02	0.86	0.02 ^a		0.71	0.69
AlN	B4	4.14	5.56	4.17	5.55		6.28
ZnO	B4	0.75	2.75	0.75	2.68		3.44

^a Reference [3].

^b Reference [18].

compare our results with the ones reported by Blaha et al. [2], with the ones obtained using the hybridized exchange potential of *Heyd-Scuseria-Ernzerhof* (*HSE*) reported in reference [3] and to the experimental values reported in references [2, 3, 17, 18].

As we stated before, we have made our calculations with the new *Wien2k 2011* code. We also repeated the calculation with the *LDA* to compare with the results obtained by Blaha et al. using the same approximation. Minor differences appear. They are always less than 3%. It is worth noting, nevertheless, that for BN the difference rises to 9%. It is evident from Table III that in any version of the code the gap values for semiconducting systems calculated with *LDA* turn out to be wrong as it very well known. The issue here is the improvement in the calculation of the gap for all the semiconducting systems consider so far. Comparing the results with the new *Wien2k 2011* code to the ones reported by Blaha et al.[2] previously, we find minor but non-negligible differences. Some improve the agreement with experiment some do not. For *MgO*, *LiF*, *BP*, *BaAs*, *BN*, *AlSb* and *ZnO* *Wien2k 2011* is in better agreement with experiment. For *Si*, *AlAs*, *SiC*, *InP*, *GaN* and *ZnS* the previously reported results by Baha et al, [2] agree better. When comparing the *Wien2k 2011* with *HSE* (See Table III) again some results turn out to agree better with experiment some do not. When *Wien2k 2011* and the experimental values are compared, we find that the overall agreement of the new code values is quite better and opens the possibility to consider interfaces and superlattices of systems containing semiconductor elements. Actually we think that, in this sense, the code opens a new direction of research that was not so clearly possible before. To see better the improvement of the *Wien2k 2011* code we present the following Figure 1.

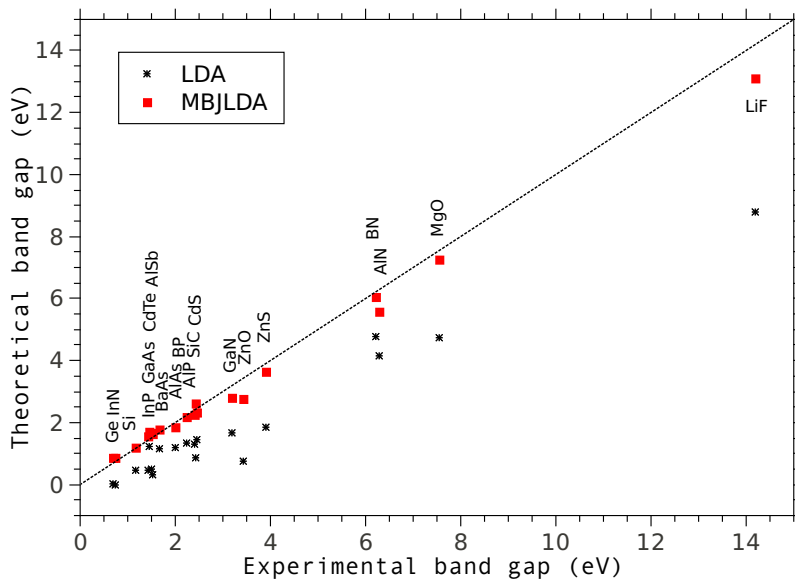


FIG. 1. Theoretical vs experimental band gaps. The are taken from Table III

Figure 1 shows the degree of improvement from the *LDA* predictions as compare to the *MBJLDA* ones. Nevertheless the predictions of *Wien2k 2011* deviate from 0-20% which points to the fact that even though the amount of progress is impressive, some more work is to be done in that direction. A point that still waits for a more convincing solution is the impossibility to optimize (to obtain a consistent value of the lattice constant) with the same potential with which the calculation is made.

V. CONCLUSIONS

In this paper we performed an analysis of the new progress done in the implementation of *DFT* whose most famous shortcoming was its impossibility to account for the experimental value of the band gap of semiconducting systems. We have calculated the band gap for all semiconductors reported in ref [2] and reference [3] and some other and compare the results among them and with experiment. We found that the new so-called *TB-MBJLDA* potential gives rise to gap values that represent an impressive progress as compare to the old *LDA* potential. This new code, the *Wien2k 2011*, allows the calculation of interfaces and superlattices with a semiconducting component with a high degree of accuracy which were impossible with the old code. For example, with the *Wien2k 2008* code, we calculated the electronic band structure of the interface *YBCO7/GaAs* and obtained [1] that two atomic planes in the GaAs side become metallic. Nevertheless since the code does not allow the correct calculation of the gap of the semiconductor, this interesting result remained uncertain [19]. In that sense, the new code opens a new field which is of interest in several disciplines as spintronics, for example. We found that the disagreement between the new code and experiment for a few semiconductors as large as 20% but on the whole, the agreement is quite good. Calculations with the *HSE* potential are also in good agreement with experiment (see Table III). The suggestion that optimization to obtain a consistent lattice parameter should be done with the *LDA* and the result used as input in the new code, was found to give results in better agreement with experiment than if one would optimize with the new potential directly. Although a justification for it is given in reference [2], we find this point

worst analyzing further.

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